XC7SH125

Bus buffer/line driver; 3-state

Rev. 01 — 4 September 2009

Product data sheet

1. General description

XC7SH125 is a high-speed Si-gate CMOS device. It provides one non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (\overline{OE}) . A HIGH at \overline{OE} causes the output to assume a high-impedance OFF-state.

2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1, SOT753, SOT886, and SOT891 package options
- ESD protection:
 - ◆ HBM JESD22-A114E: exceeds 2000 V
 - ◆ MM JESD22-A115-A: exceeds 200 V
 - ◆ CDM JESD22-C101C: exceeds 1000 V
- Specified from -40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package									
	Temperature range	Name	Description	Version						
XC7SH125GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1						
XC7SH125GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753						
XC7SH125GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886						
XC7SH125GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1 \times 0.5$ mm	SOT891						



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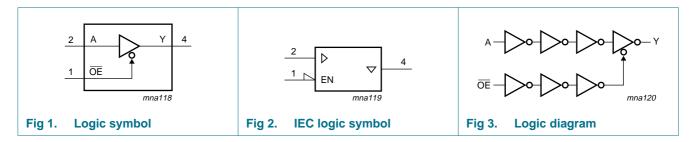
4. Marking

Table 2. Marking codes

Type number	Marking[1]
XC7SH125GW	fM
XC7SH125GV	f25
XC7SH125GM	fM
XC7SH125GF	fM

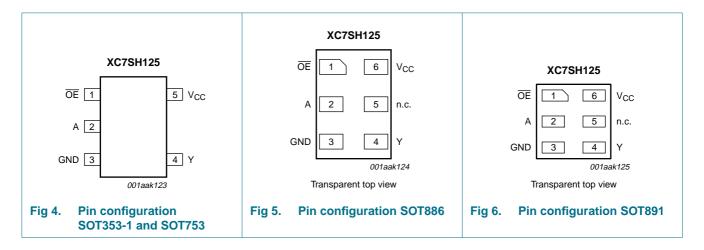
^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



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6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description				
	SOT353-1/SOT753	SOT886/SOT891					
ŌĒ	1	1	output enable input				
Α	2	2	data input				
GND	3	3	ground (0 V)				
Υ	4	4	data output				
n.c.	-	5	not connected				
V _{CC}	5	6	supply voltage				

7. Functional description

Table 4. Function table

 $H = HIGH \ voltage \ level; \ L = LOW \ voltage \ level; \ X = don't \ care; \ Z = high-impedance \ OFF-state$

Inputs OE	Output	
ŌĒ	Α	Υ
L	L	L
L	Н	Н
Н	X	Z

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V	<u>[1]</u> –20	-	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> _	±20	mA
I _O	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	75	mA
I _{GND}	ground current		-75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T_{amb} = -40 °C to +125 °C	[2] -	250	mW
	·	· · · · · · · · · · · · · · · · · · ·			

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] For TSSOP5 and SC-74A packages: above 87.5 $^{\circ}$ C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 packages: above 118 $^{\circ}$ C the value of P_{tot} derates linearly with 7.8 mW/K.

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9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		2.0	5.0	5.5	V
V_{I}	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 3.3 V \pm 0.3 V	-	-	100	ns/V
		V_{CC} = 5.0 V ± 0.5 V	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V_{IL}	LOW-level	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V_{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = -50 \mu\text{A}; V_{CC} = 2.0 \text{V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -50 \mu\text{A}; V_{CC} = 3.0 \text{V}$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \mu A$; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4.0 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 50 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 3.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_O = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
I _{OZ}	OFF-state output current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	0.25	-	2.5	-	10	μΑ
II	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	μΑ
Cı	input capacitance		-	1.5	10	-	10	-	10	pF

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11. Dynamic characteristics

Table 8. Dynamic characteristics *GND = 0 V; For test circuit see Figure 9.*

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	–40 °C t	o +125 °C	Unit
					Тур	Max	Min	Max	Min	Max	
t _{pd}	propagation	A to Y; see Figure 7	<u>[1]</u>			•	•				
	delay	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[2]								
		C _L = 15 pF		-	4.7	8.0	1.0	9.5	1.0	11.5	ns
		$C_L = 50 pF$		-	6.6	11.5	1.0	13.0	1.0	14.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C _L = 15 pF		-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		$C_L = 50 pF$		-	4.8	7.5	1.0	8.5	1.0	9.5	ns
t _{en}	enable time	OE to Y; see Figure 8	<u>[1]</u>								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[2]								
		C _L = 15 pF		-	5.0	8.0	1.0	9.5	1.0	11.5	ns
		$C_L = 50 pF$		-	6.9	11.5	1.0	13.0	1.0	14.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C _L = 15 pF		-	3.6	5.1	1.0	6.0	1.0	6.5	ns
		$C_L = 50 pF$		-	4.9	7.5	1.0	8.5	1.0	9.5	ns
t _{dis}	disable time	OE to Y; see Figure 8	<u>[1]</u>								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[2]								
		C _L = 15 pF		-	6.0	9.7	1.0	11.5	1.0	12.5	ns
		$C_L = 50 pF$		-	8.3	13.2	1.0	15.0	1.0	16.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C _L = 15 pF		-	4.1	6.8	1.0	8.0	1.0	8.5	ns
		$C_L = 50 pF$		-	5.7	8.8	1.0	10.0	1.0	11.0	ns
C_{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF; } f = 1 \text{ MHz;}$ $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	9	-	-	-	-	-	pF

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

 t_{en} is the same as t_{PZL} and t_{PZH} .

 $t_{\mbox{\scriptsize dis}}$ is the same as $t_{\mbox{\scriptsize PLZ}}$ and $t_{\mbox{\scriptsize PHZ}}.$

- [2] Typical values are measured at V_{CC} = 3.3 V.
- [3] Typical values are measured at $V_{CC} = 5.0 \text{ V}$.
- [4] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i + \Sigma (C_L \times V_{CC}{}^2 \times f_o) \text{ where:}$

 f_i = input frequency in MHz;

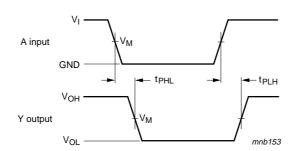
f_o = output frequency in MHz;

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts.

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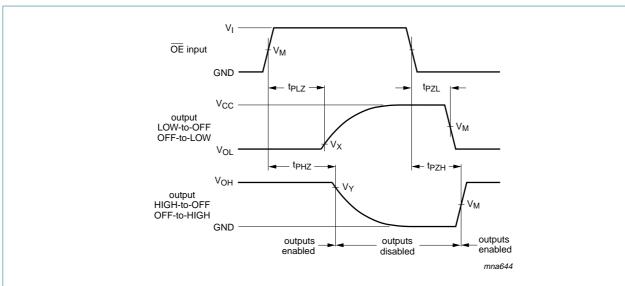
12. Waveforms



Measurement points are given in Table 9.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. Input (A) to output (Y) propagation delays



Measurement points are given in Table 9.

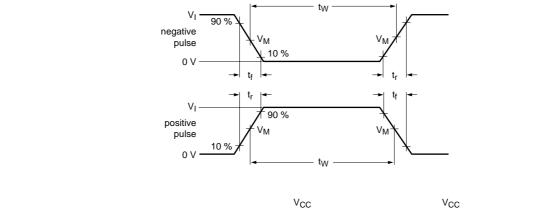
 $V_{\mbox{\scriptsize OL}}$ and $V_{\mbox{\scriptsize OH}}$ are typical output voltage levels that occur with the output load.

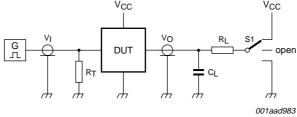
Fig 8. Enable and disable times

Table 9. Measurement points

Туре	Input	Output						
	V _M	V _M	V _X	V _Y				
XC7SH125	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.3 V	$V_{OH} - 0.3 V$				

Bus buffer/line driver; 3-state





Test data is given in Table 10.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

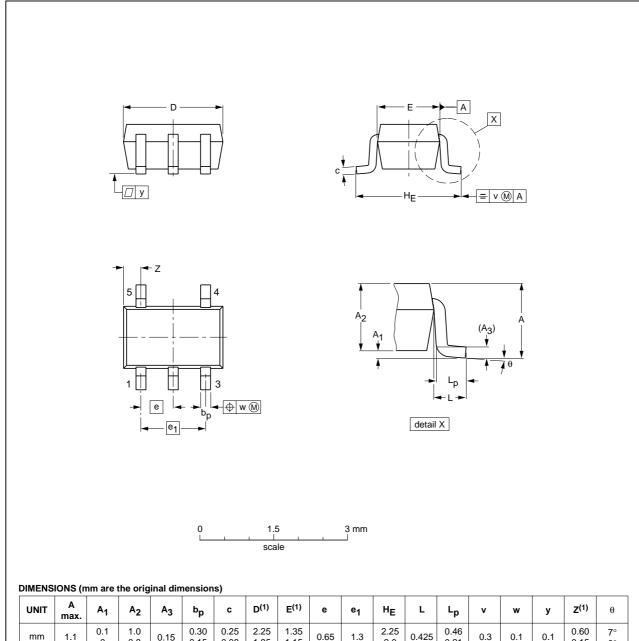
Туре	Input		Load		S1 position			
	V _I	t _r , t _f C _L		R_L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
XC7SH125	V_{CC}	≤ 3 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}	

XC7SH125 NXP Semiconductors

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	HE	L	Lp	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE	TLINE REFERENCES				EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE	
SOT353-1		MO-203	SC-88A			00-09-01 03-02-19	
					,	00 02 10	

Fig 10. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

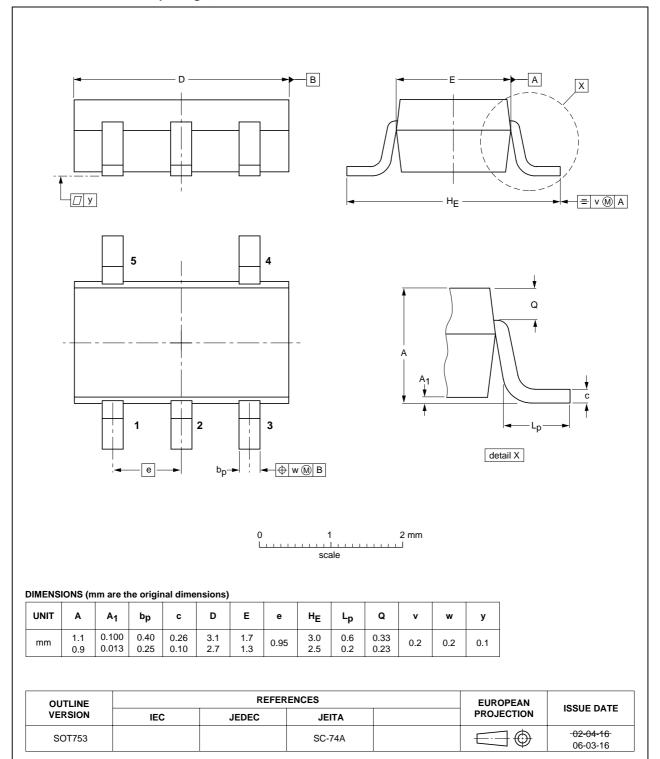


Fig 11. Package outline SOT753 (SC-74A)

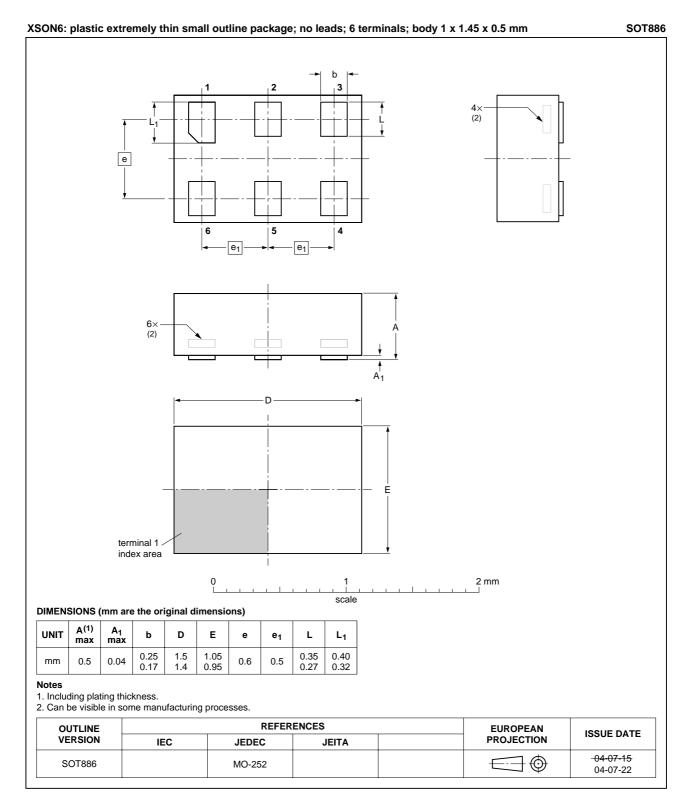


Fig 12. Package outline SOT886 (XSON6)

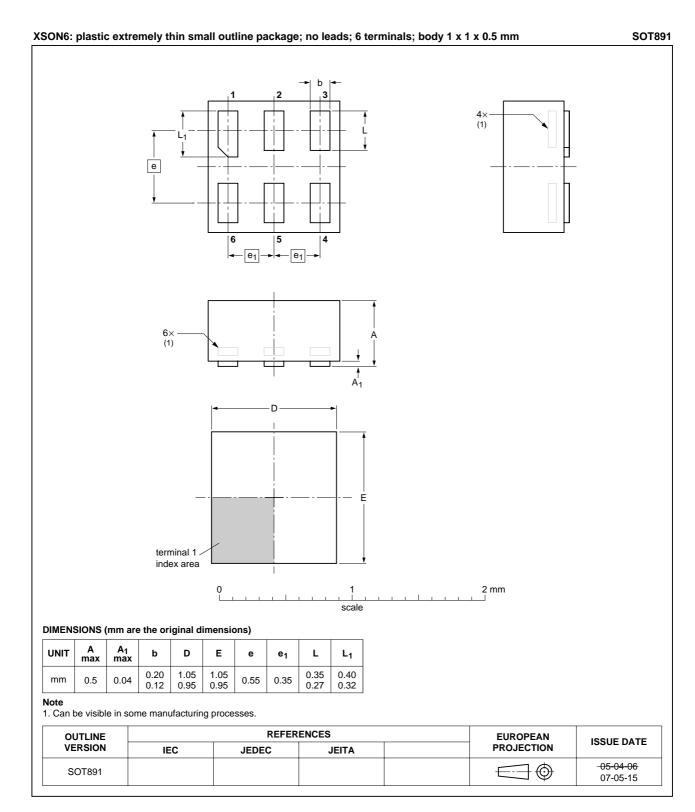


Fig 13. Package outline SOT891 (XSON6)

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
XC7SH125_1	20090904	Product data sheet	-	-

Bus buffer/line driver; 3-state

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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